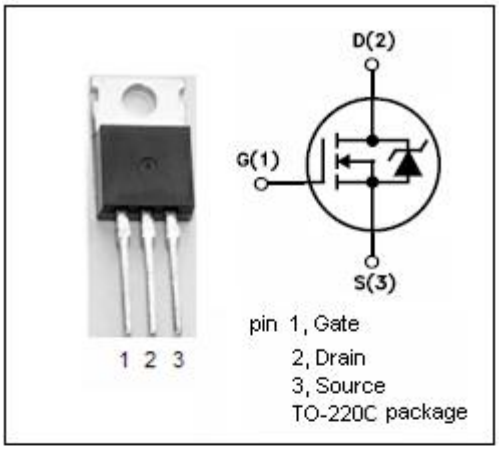
isc N-Channel Mosfet Transistor BUZ64



• FEATURES

- 11.5A, 400V
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRITION

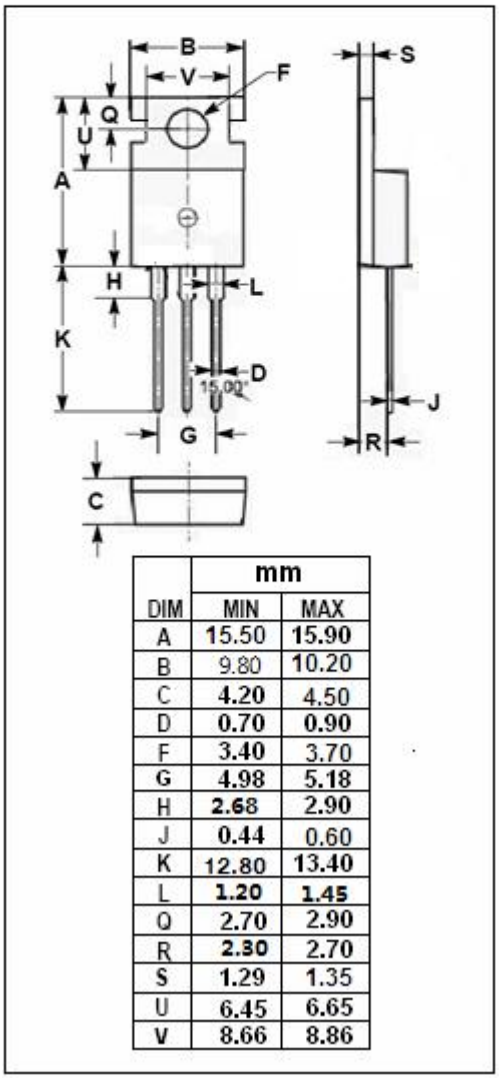
Designed for applications such as switching regulators, switching converters, motor drivers,relay drivers and drivers for high power bipolar switching transistors requiring high speed and low gate drive power.

• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	400	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ TC=37℃	11.5	A
P_{tot}	Total Dissipation@TC=25℃	125	W
T_j	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.67	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	75	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 0.25mA	400		V
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 10mA	2.1	4	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	V_{GS}= 10V; I_D= 5A		0.4	Ω
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±20V;V_{DS}= 0		±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 400V; V_{GS}= 0		250	uA
V_{SD}	Diode Forward Voltage	I_F=11A; V_{GS}= 0		1.6	V